

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-60V	25mΩ@-10V	-35A
	30mΩ@-4.5V	

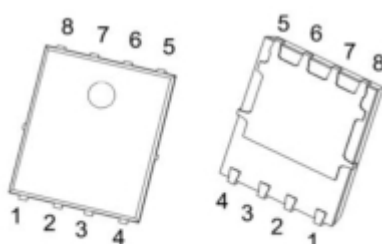
## Feature

- Fast switching speed
- Surface mount package
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

## Application

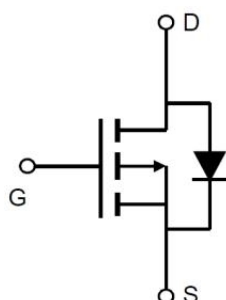
- DC-DC Converters.
- Motor Control.

## Package

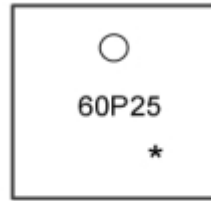


PDFNWB5×6-8L

## Circuit diagram



## Marking



**60P25**  
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**=Device Code**  
**=Month Code**

## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current(T <sub>c</sub> =25°C)	I <sub>D</sub>	-25	A
Pulse Drain Current Tested	I <sub>DM</sub>	-100	A
Maximum Power Dissipation(T <sub>c</sub> =25°C)	P <sub>D</sub>	50	W
Thermal Resistance-Junction to Case	R <sub>θJC</sub>	2.5	°C/W
Maximum Junction Temperature	T <sub>J</sub>	-55 to 150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C

## Electrical characteristics

(T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -48V, V <sub>GS</sub> = 0V			-1	uA
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	uA
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.7	-2.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A		25	35	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A		30	42	
Dynamic and Switching Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> = -30V, f=1MHz		2417		pF
Output Capacitance	C <sub>oss</sub>			179		
Reverse Transfer Capacitance	C <sub>rss</sub>			120		
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> = -30V, R <sub>L</sub> =4.7Ω, V <sub>GEN</sub> = -10V, R <sub>GEN</sub> =3Ω		9.8		nS
Turn-on Rise Time	T <sub>r</sub>			6.1		
Turn-off Delay Time	T <sub>d(off)</sub>			44		
Turn-off Fall Time	T <sub>f</sub>			12.7		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -6A		46.5	55	nC
Gate-Source Charge	Q <sub>gs</sub>			9.1		
Gate-Drain Charge	Q <sub>gd</sub>			9.2		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	I <sub>SD</sub> = -1A,V <sub>GS</sub> =0V			-1.2	V

## Typical Characteristics

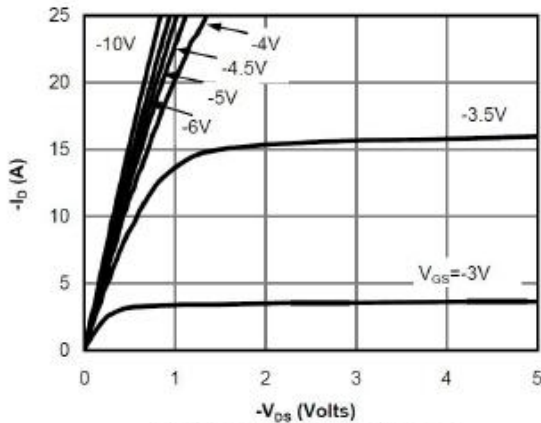


Fig 1: On-Region Characteristics

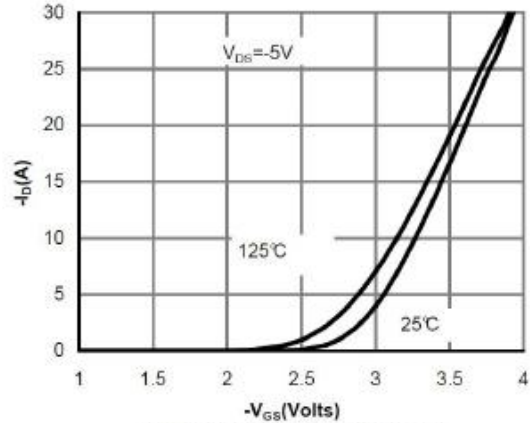


Figure 2: Transfer Characteristics

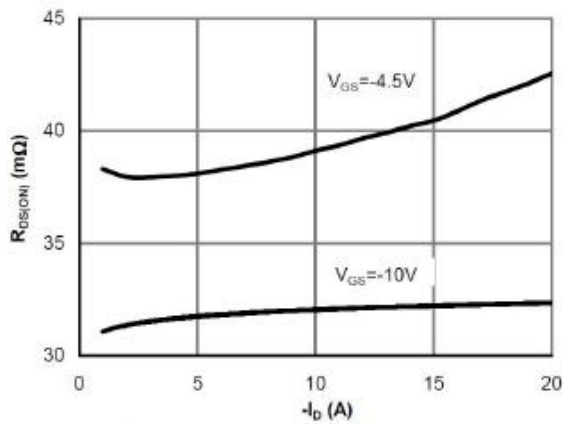


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

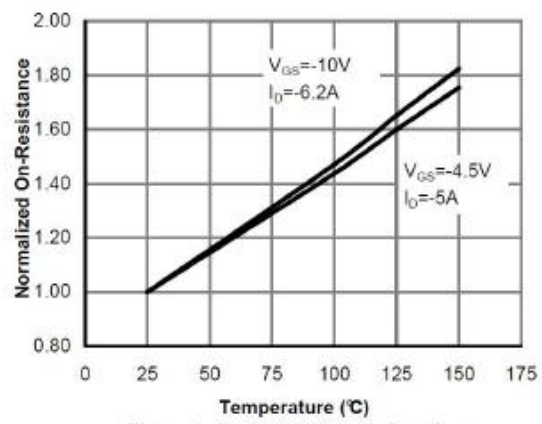


Figure 4: On-Resistance vs. Junction Temperature

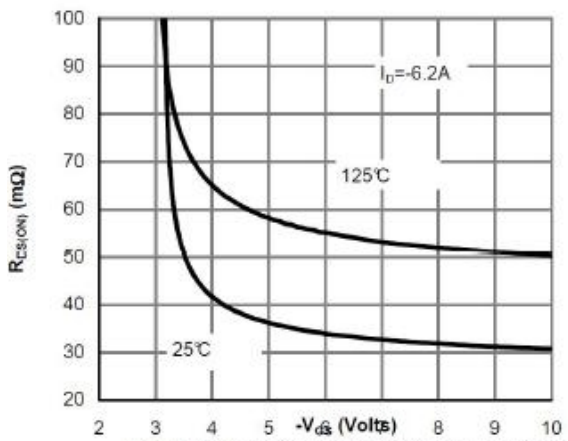


Figure 5: On-Resistance vs. Gate-Source Voltage

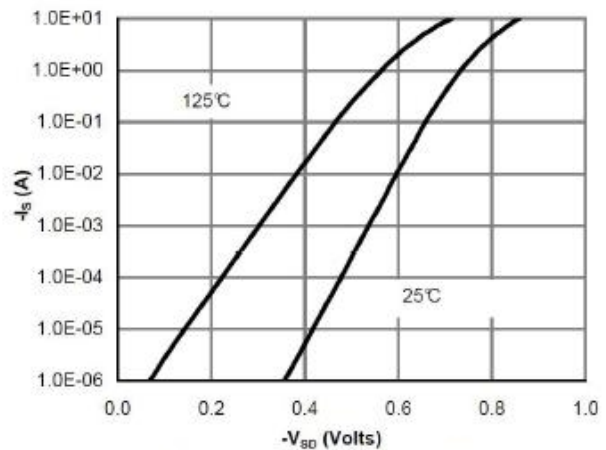


Figure 6: Body-Diode Characteristics

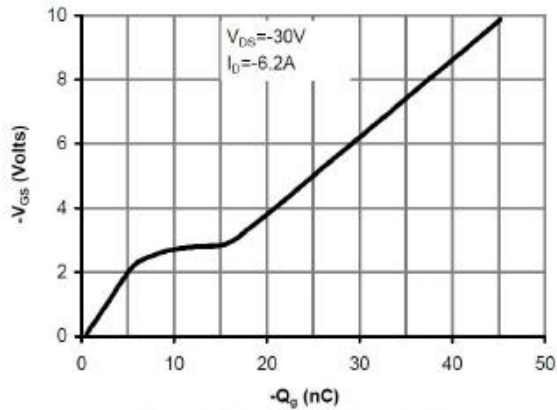


Figure 7: Gate-Charge Characteristics

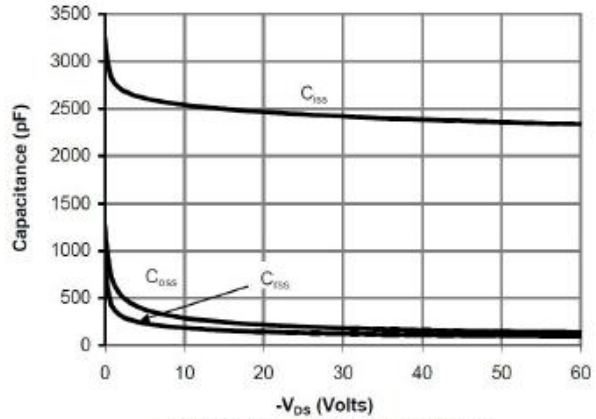


Figure 8: Capacitance Characteristics

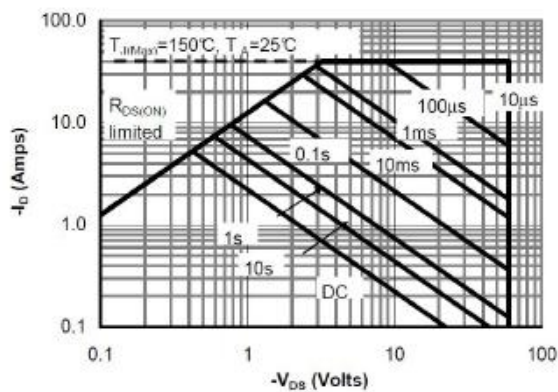


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

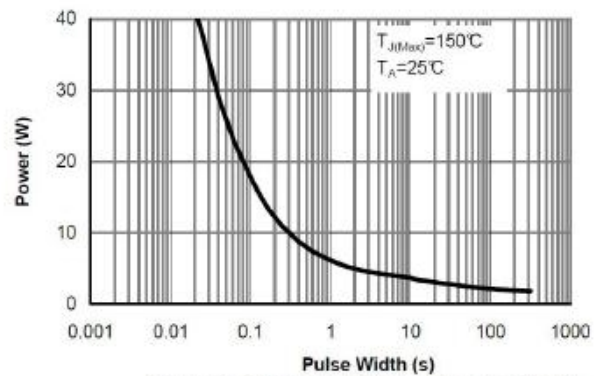


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

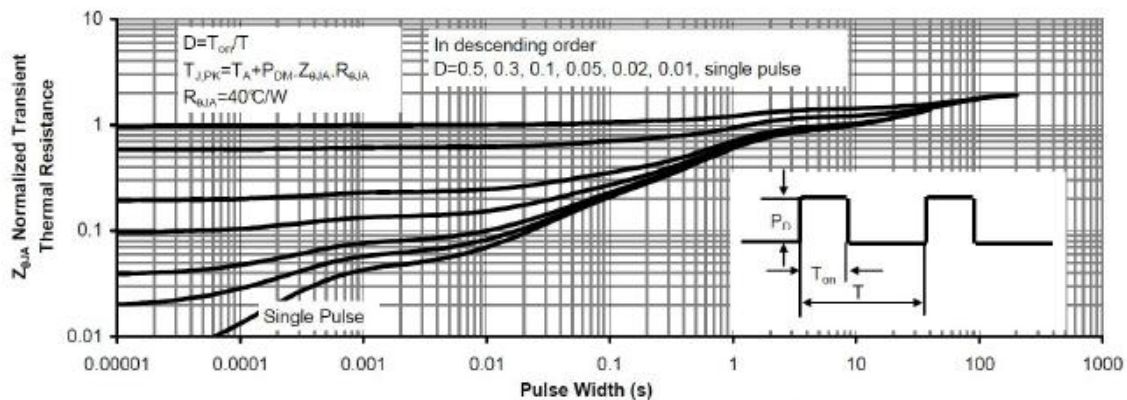
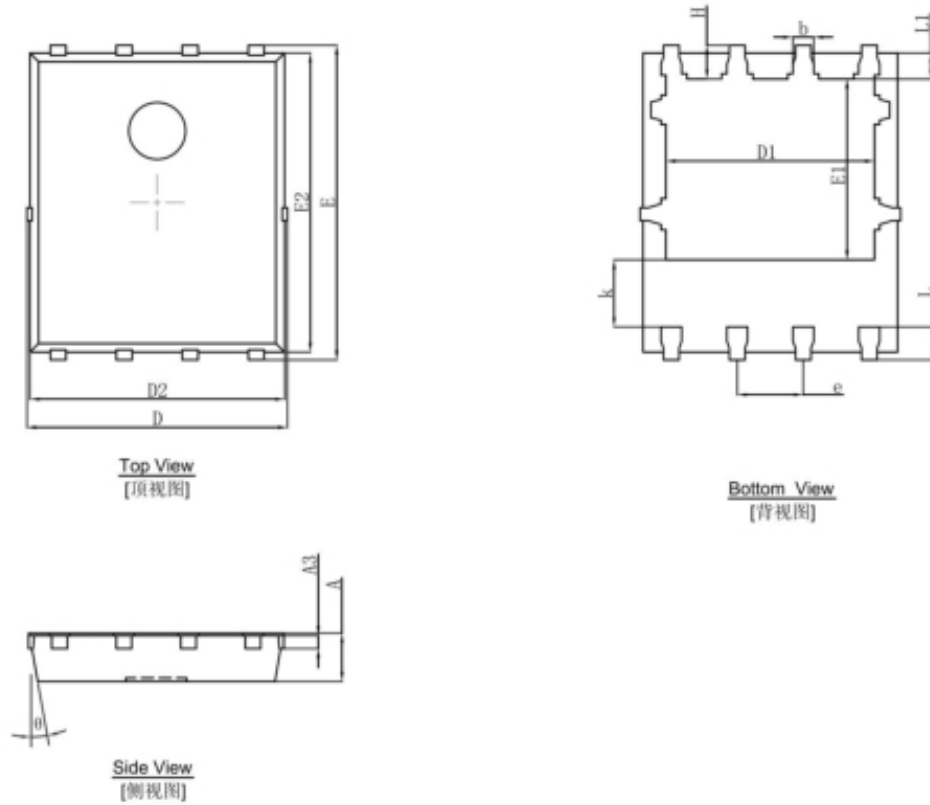


Figure 11: Normalized Maximum Transient Thermal Impedance

## PDFNWB5×6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
$\theta$	10°	12°	10°	12°